

# LS4351 N-CHANNEL MOSFET



# The LS4351 is an enhancement mode N-Channel Mosfet

The LS4351 is an enhancement mode N-Channel Mosfet designed for use as a General Purpose amplifier or switch

The hermetically sealed TO-72 package is well suited for high reliability and harsh environment applications.

(See Packaging Information).

#### LS4351 Features:

- Low ON Resistance
- Low Capacitance
- High Gain
- High Gate Breakdown Voltage
- Low Threshold Voltage

| FEATURES                                |                            |  |  |  |  |  |
|---|----------------------------|--|--|--|--|--|
| DIRECT REPLACEMENT FOR INTERSIL 2N4351  |                            |  |  |  |  |  |
| GH DRAIN CURRENT I <sub>D</sub> = 100mA |                            |  |  |  |  |  |
| HIGH GAIN                               | GAIN $g_{fS} = 1000 \mu S$ |  |  |  |  |  |
| ABSOLUTE MAXIMUM RATINGS                |                            |  |  |  |  |  |
| @ 25°C (unless otherwise noted)         |                            |  |  |  |  |  |
| Maximum Temperatures                    |                            |  |  |  |  |  |
| Storage Temperature                     | -65°C to +200°C            |  |  |  |  |  |
| Operating Junction Temperature          | -55°C to +150°C            |  |  |  |  |  |
| Maximum Power Dissipation               |                            |  |  |  |  |  |
| Continuous Power Dissipation            | 375mW                      |  |  |  |  |  |
| MAXIMUM CURRENT                         |                            |  |  |  |  |  |
| Drain to Source (Note 1)                | 100mA                      |  |  |  |  |  |
| MAXIMUM VOLTAGES                        |                            |  |  |  |  |  |
| Drain to Body                           | 25V                        |  |  |  |  |  |
| Drain to Source                         | 25V                        |  |  |  |  |  |
| Peak Gate to Source (Note 2)            | ±125V                      |  |  |  |  |  |

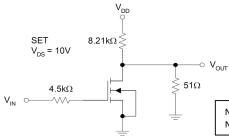
LS4351 ELECTRICAL CHARACTERISTICS @ 25°C (unless otherwise noted)

| SYMBOL              | CHARACTERISTIC                                 | MIN  | TYP. | MAX | UNITS                              | CONDITIONS                                    |  |  |  |
|---------------------|--|------|------|-----|------------------------------------|---|--|--|--|
| $BV_{DSS}$          | Drain to Source Breakdown Voltage              | 25   |      |     |                                    | $I_D = 10 \mu A$ , $V_{GS} = 0 V$             |  |  |  |
| V <sub>DS(on)</sub> | Drain to Source "On" Voltage                   |      |      | 1   | V                                  | $I_D = 2mA$ , $V_{GS} = 10V$                  |  |  |  |
| $V_{GS(th)}$        | Gate to Source Threshold Voltage               | 1    | 1 5  |     |                                    | $V_{DS} = 10V$ , $I_{D} = 10\mu A$            |  |  |  |
| I <sub>GSS</sub>    | Gate Leakage Current                           |      |      | 10  | pA                                 | $V_{GS} = \pm 30V, V_{DS} = 0V$               |  |  |  |
| I <sub>DSS</sub>    | Drain Leakage Current "Off"                    |      |      | 10  | nA                                 | $V_{GS} = 10V, V_{DS} = 10V$                  |  |  |  |
| I <sub>D(on)</sub>  | Drain Current "On"                             | 3    |      |     | mA $V_{GS} = 10V$ , $V_{DS} = 10V$ |   |  |  |  |
| <b>g</b> fs         | Forward Transconductance                       | 1000 |      |     | μS                                 | $V_{DS} = 10V$ , $I_D = 2mA$ , $f = 1MHz$     |  |  |  |
| r <sub>DS(on)</sub> | Drain to Source "On" Resistance                |      |      | 300 | Ω                                  | $V_{GS} = 10V$ , $I_{D} = 0A$ , $f = 1kHz$    |  |  |  |
| C <sub>rss</sub>    | Reverse Transfer Capacitance                   |      |      | 1.3 |                                    | $V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 140$ kHz |  |  |  |
| C <sub>iss</sub>    | Inp <mark>ut</mark> Cap <mark>ac</mark> itance |      |      | 5   | pF                                 | $V_{DS} = 10V$ , $V_{GS} = 0V$ , $f = 140kHz$ |  |  |  |
| Cdb                 | Drain to Body Capacitance                      |      |      | 5.0 |                                    | $V_{pq} = 10V$ , $f = 140$ kHz                |  |  |  |

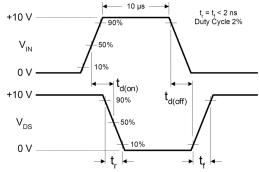
### **SWITCHING CHARACTERISTICS**

| SYMBOL              | CHARACTERISTIC                        | MAX | UNITS |  |
|---------------------|---------------------------------------|-----|-------|--|
| t <sub>d(on)</sub>  | t <sub>d(on)</sub> Turn On Delay Time |     |       |  |
| t <sub>r</sub>      | Turn On Rise Time                     | 65  | ns    |  |
| t <sub>d(off)</sub> | Turn Off Delay Time                   | 60  |       |  |
| t <sub>f</sub>      | Turn Off Fall Time                    | 100 |       |  |

## **SWITCHING TEST CIRCUIT**



TIMING WAVEFORMS



 $Note \ 1 - Absolute \ maximum \ ratings \ are \ limiting \ values \ above \ which \ LS4351 \ service ability \ may \ be \ impaired.$ 

Note 2 - Device must not be tested at ±125V more than once or longer than 300ms.

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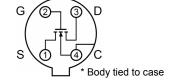
Email: <a href="mailto:chipcomponents@micross.com">chipcomponents@micross.com</a>
Web: <a href="http://www.micross.com/distribution">http://www.micross.com/distribution</a>

Available Packages:

LS4351 in TO-72 LS4351 in bare die.

Please contact Micross for full package and die dimensions

TO-72 (Bottom View)



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